

CLAIMS

1. Method for producing a multilayer structure comprising at least first and second layers (110a, 110b, 210a, 210b) called main layers, connected to each other through a stacking of at least two stress adaptation layers (120, 130, 220, 230) and having a
5 determined structure stress, wherein:

a) the first main layer is provided with a first stress adaptation layer, and one of the second main layer and the first stress adaptation layer is provided
10 with at least a second stress adaptation layer,

b) an assembly of the first and second main layers is performed via stress adaptation layers, wherein the first and second adaptation layers are produced in materials and with thicknesses such that at the end of
15 the method, said determined structure stress is obtained in the structure.

2. The method according to claim 1, wherein said assembly of first and second main layers comprises an
20 adherence bond.

Sub A1
~~3. The method according to claim 1 or 2, wherein the first and second adaptation layers are produced in materials and with thicknesses such as the stresses
25 with the first and second main layers are of opposite sign, respectively.~~

4. The method according to claim 1, wherein after

step b) a heat treatment with sufficient temperature and duration is performed for adjusting said determined structure stress in the structure.

5 The method according to claim 1, wherein at least one of the stress adaptation layers is surmounted by at least a so-called intermediate layer.

6 The method according to claim 1 or 2, wherein said assembly comprises a molecular adhesion bond
10 between layers.

7 The method according to claim 6, wherein before step b), a preparation of the layers to be combined by molecular bonding is performed for adjusting a surface
15 condition of these layers.

8 The method according to claim 6, wherein during step b), the molecular bonding is performed at room temperature.
20

9 The method according to claim 1, wherein said assembly comprises a bond implementing at least one bonding technique selected from: brazing, welding, interdiffusion between layers, and bonding with an
25 adhesive substance.

10 The method according to claim 1, wherein said assembly occurs via an adhesion layer.

30 11 The method according to claim 1, wherein

during step a), the first stress adaptation layer (130, 220) is formed on the first main layer (110a, 210a) and the second stress adaptation layer (120, 230) is formed on the second main layer (110b, 210b), and wherein
5 during step b), molecular bonding is performed between the stress adaptation layers.

12. The method according to claim 1, wherein the first and second stress adaptation layers are formed on the first main layer and the bonding occurs between the
10 second main layer and one of the first and second surface stress adaptation layers.

13. The method according to claim 1, further comprising a thinning step in at least one of the main
15 layers after assembly.

14. The method according to claim 1 or 13, wherein the thinning step includes a separation step for fracturing along the fracture area.
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15. The method according to claim 14, comprising at least an implantation of gas species in at least one of the first or second main layers or at least one of the first or second adaptation layers in order to form
25 a fracture area (112, 212) therein, and a thinning step including a thermal and/or mechanical treatment.

16. The method according to claim 14 or 15, wherein the obtained structure stress after thinning is
30 such that it participates in the separation at the

fracture area.

17. The method according to claim 1, wherein at least one stress adaptation layer is formed by depositing material according to a deposition method selected from spray, epitaxy, chemical deposition, methods such as chemical vapor deposition, low pressure vapor deposition and plasma-aided vapor deposition.

18. The method according to claim 1, wherein at least one stress adaptation layer is obtained by surface oxidization of a main layer.

19. The method according to claim 1, wherein at least one stress adaptation layer is obtained by implanting species in a main layer.

20. The method according to claim 1, wherein the main layers are produced in at least one material selected from silicon, germanium, silicon carbide, III-V type semiconductors, II-VI type semiconductors, glass, supraconductors, diamond, ceramic materials (LiNbO_3 , LiTaO_3), and quartz and wherein the stress adaptation layers are produced in at least one material selected from SiO_2 , SiN , Si_3N_4 , TiN , metals, metal alloys, and diamond or materials from one of the main layers.

21. A multilayer structure with controlled internal stresses comprising, in this order, a stack of

at least a first main layer (110, 210a), of at least one first stress adaptation layer (130, 220) in contact with the first main layer, with at least a second stress adaptation layer (120, 230) in contact with said
 5 first stress adaptation layer and a second main layer (110b, 210b) in contact with the second stress adaptation layer, the first and second stress adaptation layers having contact stresses with the first and second main layers, with the opposite sign,
 10 respectively.

22. The structure according to claim 21, characterized in that the stack further includes a bonding layer located between the stress adaptation
 15 layers or between one of the stress adaptation layers and a matching main layer.

23. The structure according to claim 21, having a suspended membrane, the suspended membrane (244)
 20 including at least a portion of one of the first and second main layers, released from the second main layer, from the first main layer, respectively.

24. The structure according to claim 23, ~~wherein~~
 25 the suspended membrane (244) further comprises at least one ~~supraconducting~~ material layer (248) covering said portion of one of the first and second main layers.

Sub A2